



L	Hits	Search Text	DB	Time stamp
Number	0	420/257 262 264 762 762 gglg and	USPAT;	2004/04/17
1	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric	US-PGPUB; EPO; JPO;	14:34
2	588	adj layer) and (control adj gate) 438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/04/17 14:34
3	7	layer) and (control adj gate) 438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/04/17 14:36
4	3	layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) 438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:15
5	. 1	@ad<20000228 6136652.pn. and (oxide same "40")	USPAT; US-PGPUB; EPO; JPO;	2004/04/17 15:12
6	1	6136652.pn. and (oxide same "40" adj angstroms)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:12
7	0	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and ((p adj channel) or p-channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:16
8	3	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:17
9		438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and (erase same volt\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:21
10	1	6136652.pn. and (erase same volt\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:23
11	1	6136652.pn. and (erase same volt\$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:30
12	0	6245613.pn. and (erase same volt\$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:30
13	0	6246089.pn. and (erase same volt\$3 same (floating adj gate))	USPAT; US-PGPUB; EPO; JPO;	2004/04/17 15:31
-	790596	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/26 14:01
-	1819	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 14:38





-	53		USPAT;	2003/07/11
-		floating adj gate and dielectric adj	US-PGPUB;	19:01
	•	layer and control adj gate) and oxide adj	EPO; JPO;	
	791060	layer with "50" adj angstroms memory adj cell and oxide adj layer and	DERWENT USPAT;	2003/07/10
-	791000	floating adj gate and dielectric adj	US-PGPUB;	17:10
		layer and control gate	EPO; JPO;	17.10
		l and concret gate	DERWENT	
_	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/11
		floating adj gate and dielectric adj	US-PGPUB;	19:02
		layer and control adj gate) and oxide adj	EPO; JPO;	
		layer with "50" adj angstroms and .25 adj	DERWENT	
		micron adj gate		
-	. 43	(memory adj cell and oxide adj layer and	USPAT;	2003/11/13
		floating adj gate and dielectric adj	US-PGPUB; EPO; JPO;	11:11
		layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or	DERWENT	
		quarter adj micron adj gate	DEIXWEIVI	
_	l 0		USPAT;	2003/07/11
	ľ	floating adj gate and dielectric adj	US-PGPUB;	19:04
		layer and control adj gate) and oxide adj	EPO; JPO;	
		layer with "50" adj angstroms and (.25 or	DERWENT	
		quarter) adj micron		
-	15	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:35
	,	layer and control adj gate) and (.25 or	EPO; JPO; DERWENT	
	0	quarter) adj micron (memory adj cell and oxide adj layer and	USPAT;	2003/07/11
-		(memory ad) cell and oxide ad) layer and floating adj gate and dielectric adj	US-PGPUB;"	19:28
		layer and control adj gate) and oxide adj	EPO; JPO;	
		layer with "50" adj angstroms and (.25 or	DERWENT	
-		quarter) adj micron		
-	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:32
		layer and control adj gate) and oxide adj	EPO; JPO;	
		layer with "50" adj angstroms and (.18 or	DERWENT	
	. 0	quarter) adj micron (memory adj cell and oxide adj layer and	USPAT;	2003/07/12
-		(memory adj ceri and oxide adj layer and floating adj gate and dielectric adj	US-PGPUB;	11:33
		layer and control adj gate) and oxide adj	EPO; JPO;	
		layer with "50" adj angstroms and (.18)	DERWENT	
]	adj micron		
-	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:33
		layer and control adj gate) and (.18) adj	EPO; JPO;	
	0	micron (memory adj cell and oxide adj layer and	USPAT;	2003/07/12
-	I	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj	US-PGPUB;	11:33
	· ·	layer and control adj gate) and (.15) adj	EPO; JPO;	
		micron	DERWENT	
-	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:33
		layer and control adj gate) and (.1) adj	EPO; JPO;	
	_	micron	DERWENT	2002/07/12
-	0	(.1) adj micron	USPAT; US-PGPUB;	2003/07/12 11:34
			EPO; JPO;	11.37
			DERWENT	
_	0	(.18) adj micron	USPAT;	2003/07/12
	.		US-PGPUB;	11:34
	1		EPO; JPO;	
			DERWENT	
-	0	(.25) adj micron	USPAT;	2003/07/12
			US-PGPUB;	11:34
			EPO; JPO; DERWENT	
_	0	 (memory adj cell and oxide adj layer and	USPAT;	2003/07/12
-	ľ	floating adj gate and dielectric adj	US-PGPUB;	11:35
	1	layer and control adj gate) and (.25) adj	EPO; JPO;	
	1	micron	DERWENT	
		· · · · · · · · · · · · · · · · · · ·		



			<u> </u>	
-	15	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:36
		layer and control adj gate) and (.25 or	EPO; JPO;	
		quarter) adj micron	DERWENT	0000/07/10
-	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj layer and control adj gate) and (.25) adj	US-PGPUB; EPO; JPO;	11:36
		micron	DERWENT	
	43	438/257.CCLS. AND (memory adj cell and	USPAT;	2003/07/13
_	13	oxide adj layer and floating adj gate and	US-PGPUB;	16:25
		dielectric adj layer and control adj	EPO; JPO;	10.20
		gate) and oxide adj layer with "50" adj	DERWENT	
		angstroms and .25 or quarter adj micron		
		adj gate		
-	43	257/315,316.CCLS. AND 438/257.CCLS. AND	USPAT;	2003/07/13
		(memory adj cell and oxide adj layer and	US-PGPUB;	16:26
		floating adj gate and dielectric adj	EPO; JPO;	
		layer and control adj gate) and oxide adj	DERWENT	
	1	layer with "50" adj angstroms and .25 or		i
		quarter adj micron adj gate	******	0000/11/10
_	48	memory adj cell and oxide adj layer and	USPAT;	2003/11/13 12:16
	1	floating adj gate and dielectric adj layer and control adj gate and oxide adj	US-PGPUB; EPO; JPO;	12:16
		layer with "50" adj angstroms and .25 or	DERWENT	
		quarter adj micron adj gate	DUIMANIAT	
-	1797	memory adj cell and oxide adj layer and	USPAT;	2003/11/13
		floating adj gate and dielectric adj	US-PGPUB;	12:08
		layer and control adj gate and oxide adj	EPO; JPO;	
		layer and "50" adj angstroms and .25 or	DERWENT	
		quarter adj micron		
_	0	(memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
		and (floating adj gate) and (dielectric	US-PGPUB;	12:22
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("50" adj angstroms) and (.25 or quarter adj micron	DERWENT	
		adj gate))		
_	57	(memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
		and (floating adj gate) and (dielectric	US-PGPUB;	18:04
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("50" adj	DERWENT	
	·	angstroms))		
-	0	257/315,316.ccls and (memory adj cell)	USPAT;	2003/11/13
		and (oxide adj layer) and (floating adj	US-PGPUB;	16:38
		gate) and (dielectric adj layer) and	EPO; JPO;	
		(control adj gate) and ((oxide adj layer) with ("50" adj angstroms))	DERWENT	
_	9	438/264,762,763.ccls. and (memory adj	USPAT;	2003/11/13
		cell) and (oxide adj layer) and (floating	US-PGPUB;	18:01
1		adj gate) and (dielectric adj layer) and	EPO; JPO;	-
		(control adj gate) and ((oxide adj layer)	DERWENT	
1		with ("50" adj angstroms))		
-	. 0	438/264,762,763.ccls. and (memory adj	USPAT;	2003/11/29
1		cell) and (oxide adj layer) and (floating	US-PGPUB;	16:04
		adj gate) and (dielectric adj layer) and	EPO; JPO;	
		(control adj gate) and ((oxide adj layer)	DERWENT	
1_	0	with ("23" adj angstroms)) 6515328.pn. and (p adj channel)	USPAT;	2003/11/13
_		ooloozo.pii. and (p ad) chaimel/	US-PGPUB;	17:41
			EPO; JPO;	
1			DERWENT	
-	0	6515328.pn. and (p adj channel or	USPAT;	2003/11/13
		positiv\$3 adj dop\$3)	US-PGPUB;	17:43
		-	EPO; JPO;	
	·		DERWENT	
-	0	6515328.pn. and ((p adj channel) or	USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:44
1			EPO; JPO;	
_	o	5852311.pn. and ((p adj channel) or	DERWENT USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:45
		/Ferrent and mobile//	EPO; JPO;	
			DERWENT	
	•	·, · · · · · · · · · · · · · · · · ·		



_	0	5869370.pn. and ((p adj (positiv\$3 adj dop\$3))	channel)	or	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:46
-	0		channel)	or	DERWENT USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))			US-PGPUB; EPO; JPO; DERWENT	17:46
_	. 0	6383939.pn. and ((p adj (positiv\$3 adj dop\$3))	channel)	or	USPAT; US-PGPUB;	2003/11/13 17:47
_	0	6316316.pn. and ((p adj	channel)	or	EPO; JPO; DERWENT USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	,		US-PGPUB; EPO; JPO; DERWENT	17:47
-	1	6456535.pn. and ((p adj (positiv\$3 adj dop\$3))	channel)	or	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:48
_	. 0	6261906.pn. and ((p adj	channel)	or	DERWENT USPAT;	2003/11/13 17:48
		(positiv\$3 adj dop\$3))			US-PGPUB; EPO; JPO; DERWENT	
_	0	6261906.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	USPAT; US-PGPUB; EPO; JPO;	2003/11/13
-	0	5852311.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	DERWENT USPAT; US-PGPUB;	2003/11/13 17:49
_	0	5869370.pn. and ((p adj	channel)	or	EPO; JPO; DERWENT USPAT;	2003/11/13
		(positiv\$3 same dop\$3))			US-PGPUB; EPO; JPO; DERWENT	17:50
-	0	5852311.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	USPAT; US-PGPUB; EPO; JPO;	2003/11/13
-	0	5869370.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:50
-	0	6515328.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:51
-	0	6316316.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	DERWENT USPAT; US-PGPUB;	2003/11/13 17:51
-	1	6456535.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	EPO; JPO; DERWENT USPAT; US-PGPUB;	2003/11/13 17:51
_	0		channel)	or	EPO; JPO; DERWENT USPAT;	2003/11/13
		(positiv\$3 same dop\$3))			US-PGPUB; EPO; JPO; DERWENT	17:55
-	0	6372651.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:56
_	. 0	6383939.pn. and ((p adj (positiv\$3 same dop\$3))	channel)	or	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:56
_	0	6515328.pn. and ((p adj (positiv\$3 same dop\$3))		or	DERWENT USPAT; US-PGPUB;	2003/11/13 17:57
					EPO; JPO; DERWENT	



-	0 6316316.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; 2003/11/1 US-PGPUB; 17:57 EPO; JPO;	3
-	6456535.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; 2003/11/1 US-PGPUB; 17:57 EPO; JPO;	3
-	6249819.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; 2003/11/1 US-PGPUB; 17:58 EPO; JPO;	3
-	20030201477.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT 2003/11/1 USPAT; 2003/11/1 US-PGPUB; 17:58 EPO; JPO;	3
-	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms)) and ((p adj	DERWENT USPAT; 2003/11/1 US-PGPUB; 18:02 EPO; JPO; DERWENT	3
- 1	channel) or (p-channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("50" adj angstroms)) and ((p-channel) or (p adj	USPAT; 2003/11/2 US-PGPUB; 13:44 EPO; JPO; DERWENT	5
_ 30	and (floating adj gate) and (dielectric adj layer) and (control adj gate) and	USPAT; 2003/11/1 US-PGPUB; 18:10 EPO; JPO;	.3
-	<pre>((p-channel) or (p adj channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel))</pre>	DERWENT USPAT; 2003/11/2 US-PGPUB; 14:47 EPO; JPO; DERWENT	5
-	("40" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; 2003/11/2 US-PGPUB; 14:18 EPO; JPO; DERWENT	5
_ 1	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("30" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; 2003/11/2 US-PGPUB; 14:53 EPO; JPO; DERWENT	5
_ 1	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("23" adj angstroms)) and ((p-channel) or (p adj channel))	USPAT; 2003/11/2 US-PGPUB; 14:54 EPO; JPO; DERWENT	5
-	6515328.pn. and (p-channel or p adj channel)	USPAT; 2003/11/2 US-PGPUB; 14:02 EPO; JPO;	6
-	6372651.pn. and (p-channel or p adj channel)	DERWENT USPAT; 2003/11/2 US-PGPUB; 14:03 EPO; JPO; DERWENT	6
-	6383939.pn. and (p-channel or p adj channel)	USPAT; 2003/11/2 US-PGPUB; 14:04 EPO; JPO; DERWENT	6
-	6383939.pn. and (p-channel or p adj channel or p channel)	USPAT; 2003/11/2 US-PGPUB; 14:04 EPO; JPO; DERWENT	6





-	0	438/257,263, 264,762,763.ccls. and	USPAT;	2004/04/17
		(memory adj cell) and (oxide adj layer)	US-PGPUB;	14:35
		and (floating adj gate) and (dielectric	EPO; JPO;	
		adj layer) and (control adj gate) and	DERWENT	
		((oxide adj layer) with ("40" adj		
		angstroms))		
-	0	438/257,263, 264,762,763.ccls. and	USPAT;	2003/11/29
		(memory adj cell) and (oxide adj layer)	US-PGPUB;	16:05
		and (floating adj gate) and (dielectric	EPO; JPO;	
		adj layer) and (control adj gate) and	DERWENT	
		(oxide adj layer)		
_	0	438/257,263, 264,762,763.ccls. and	USPAT;	2004/04/17
		(memory adj cell) and (oxide adj layer)	US-PGPUB;	14:33
		and (floating adj gate) and (dielectric	EPO; JPO;	
		adj layer) and (control adj gate)	DERWENT	